

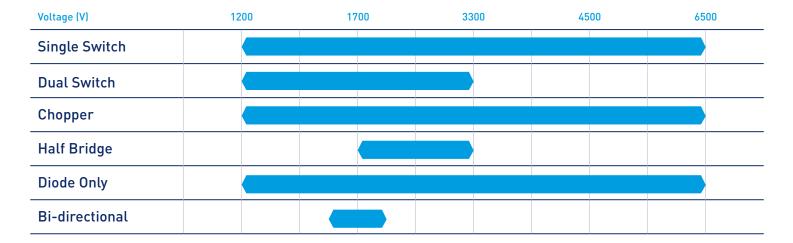
IGBT Overview

IGBT



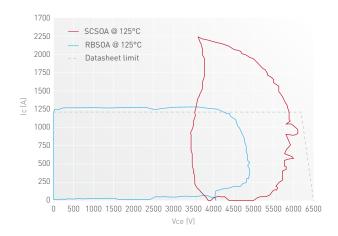
- With manufacturing facilities in the UK and China, we are able to offer mass production capabilities, engineering samples and collaborative R&D projects
- We are a vertically integrated facility with device design, wafer fab, packaging, qualification and testing available on site
- Our R&D centre has dedicated engineers for design and simulation using the latest software packages
- No matter your application, all our products can be fully customised to meet your requirements with alternative devices, materials, and interconnect technology
- Using our relationships with various suppliers we offer our clients application specific silicon products
- We have a range of industry standard packages and footprints allowing you to increase your supply chain security
- In addition to our own silicon devices we are able to incorporate silicon and wide band gap devices from a range of world leading suppliers





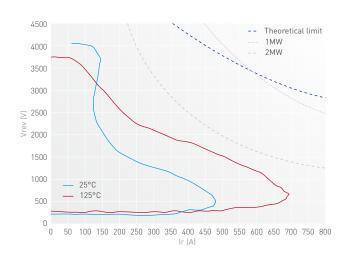
IGBT SOA

DIM600ASM65-T000
IGBT Safe Operating Area Limit



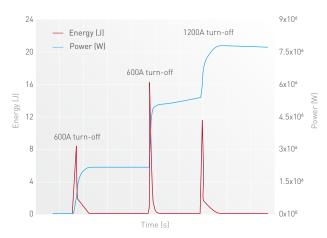
FRD SOA

FRD RBSOA



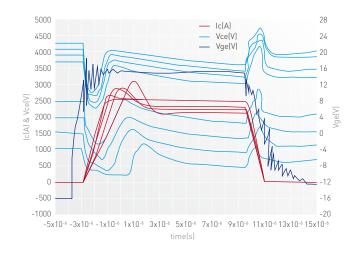
RBSOA E&P

DIM600ASM65-T000 Switching Energy to Power



SCSOA

DIM600ASM65T000 10002000 #864 (13kV FRD) Cge=0nF, Rgon=1R85, Rgoff=10R & Tj=125°C



Dynex Semiconductor Ltd Doddington Road, Lincoln LN6 3LF United Kingdom

Email: contactus@dynexsemi.com
Main switchboard: +44 (0)1522 500 500
Sales & Marketing: +44 (0)1522 502 901



f /DynexSemiconductor

in Dynex Semiconductor Ltd

